

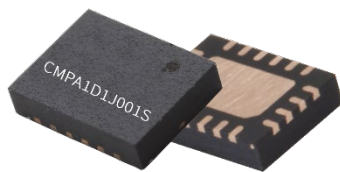
# CMPA1D1J001S

12.7 – 18 GHz, 1 W GaN HPA

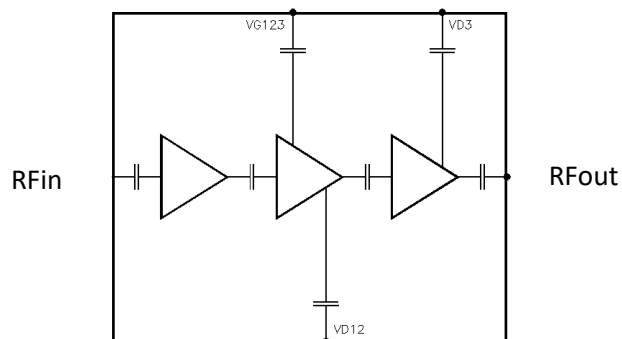
## Description

The CMPA1D1J001S is a 1W package MMIC HPA utilizing the high performance, 0.15um GaN on SiC production process. The CMPA1D1J001S operates from 12.7-18 GHz and supports both radar and communication applications within both military and commercial markets. The CMPA1D1J001S achieves 1 W of saturated output power with 23 dB of large signal gain and typically 30% power-added efficiency under CW operation.

Packaged in a 4x3 mm plastic overmold QFN, the CMPA1D1J001S provides superior broadband performance and environmental robustness in a small form factor allowing customers to improve SWaP-C benchmarks in their next-generation systems.



**Figure 1. CMPA1D1J001S**



**Figure 2. Functional Block Diagram**

## Features

- Psat: 1 W
- PAE: 30 %
- LSG: 23 dB
- S21: 27 dB
- S11: -10 dB
- S22: -8 dB
- CW operation
- Small 4 x 3 mm footprint

Note: Features are typical performance across frequency under 25C operation. Please reference performance charts for additional information.

## Applications

- Military and Commercial Radar and Communications
- General Purpose Broadband Amplifier



### Absolute Maximum Ratings

Parameter	Symbol	Units	Value	Conditions
Drain to Source Voltage	$V_{DSS}$	V	84	
Drain Voltage	$V_D$	V	28	
Gate Voltage	$V_G$	V	-8, +2	
Drain Current	$I_D$	A	0.8	
Gate Current	$I_G$	mA	1.0	
Input Power	$P_{in}$	dBm	10	
Dissipated Power	$P_{diss}$	W	4.4	85°C
Storage Temperature	$T_{stg}$	°C	-55, +150	
Mounting Temperature	$T_J$	°C	260	30 seconds
Junction Temperature	$T_J$	°C	225	
Output Mismatch Stress	VSWR	$\Psi$	5:1	

### Recommended Operating Conditions

Parameter	Symbol	Units	Typical Value	Conditions
Drain Voltage	$V_d$	V	22	
Gate Voltage	$V_g$	V	-2.0	
Drain Current	$I_{dq}$	mA	30	
Input Power	$P_{in}$	dBm	8	
Case Temperature	$T_{case}$	°C	-40 to 85	

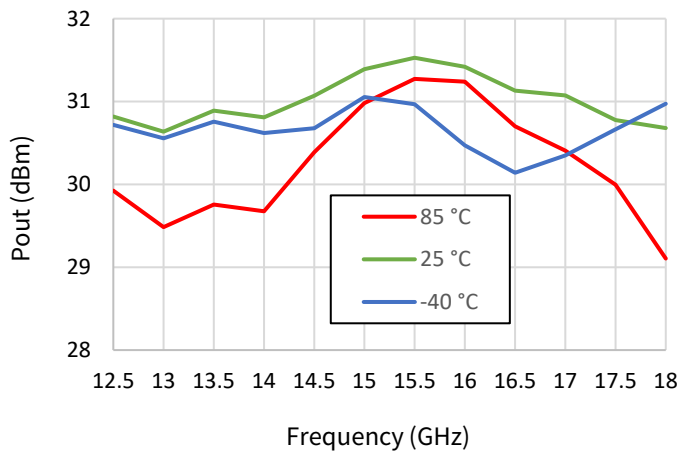
### RF Specifications

Test conditions unless otherwise noted:  $V_d=22$  V,  $I_{dq}=30$ mA, CW,  $P_{in} = 8$  dBm,  $T_{base}=25$ °C

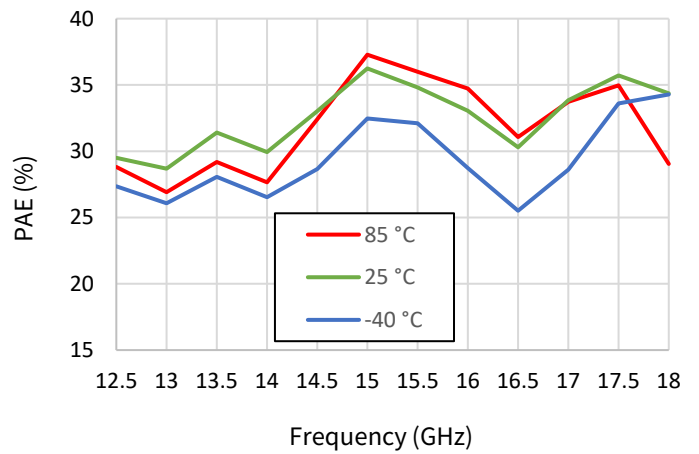
Parameter	Units	Frequency	Min	Typical	Max	Conditions
Frequency	GHz		13		18	
Output Power	dBm	12.7		30.5		
		15.5		31.5		
		18		30.5		
Power-added Efficiency	%	12.7		28		
		15.5		35		
		18		34		
LSG	dB	12.7		22.5		
		15.5		23.5		
		18		22.5		
Small-Signal Gain	dB	12.7		27		Pin = -20 dBm
		15.5		30		
		18		24		
Input Return Loss	dB			-10		Pin = -20 dBm
Output Return Loss	dB			-8		Pin = -20 dBm

Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz

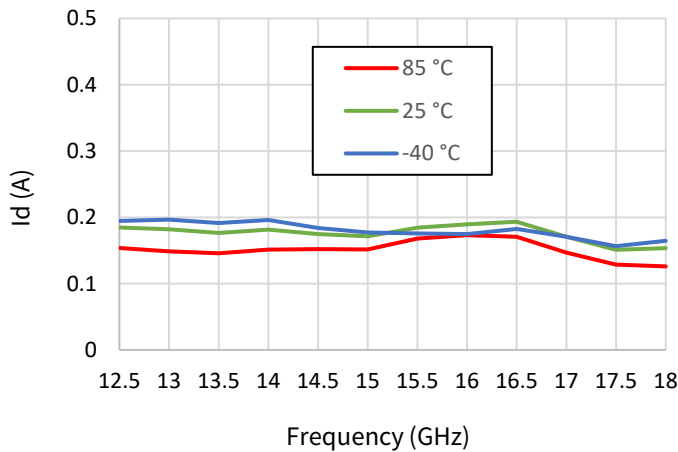
**Figure 3: Pout v. Frequency v. Temperature**



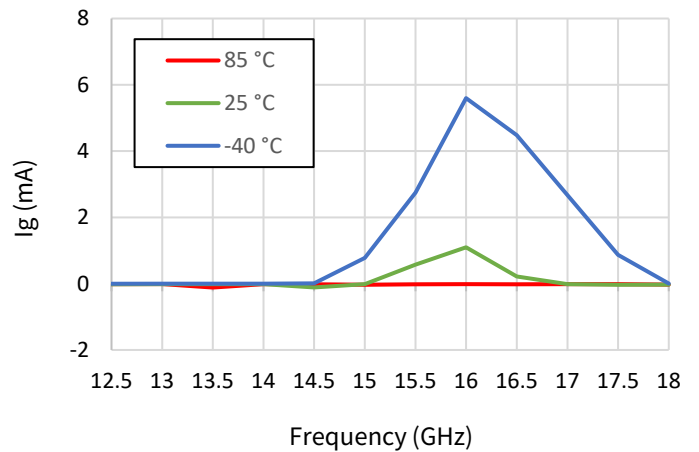
**Figure 4: PAE v. Frequency v. Temperature**



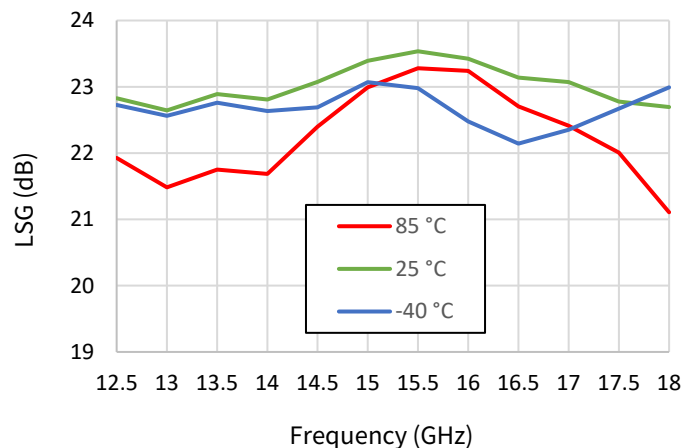
**Figure 5: Id v. Frequency v. Temperature**



**Figure 6: Ig v. Frequency v. Temperature**

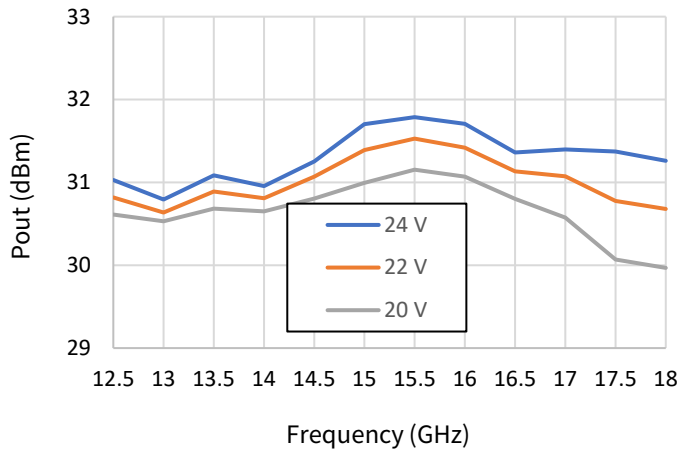


**Figure 7: LSG v. Frequency v. Temperature**

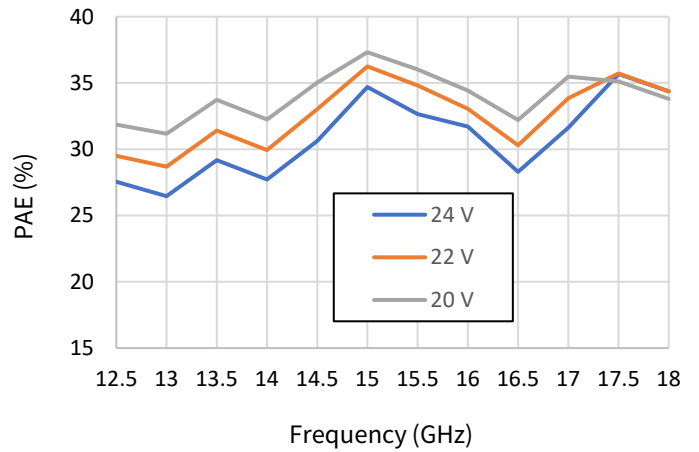


Test conditions unless otherwise noted: Vd=22 V, Idq=30mA, CW, Pin = 8 dBm, T<sub>base</sub>=25 °C, Frequency: 15.5GHz

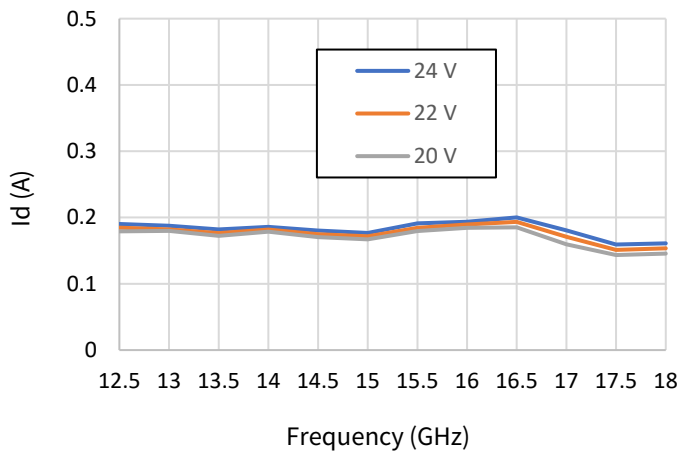
**Figure 8: Pout v. Frequency v. Vd**



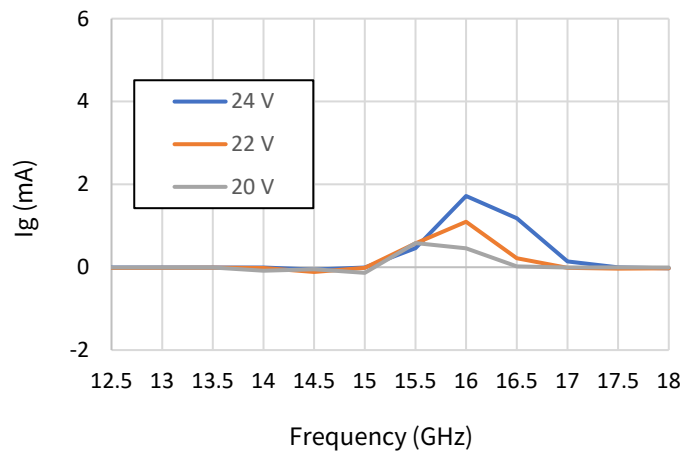
**Figure 9: PAE v. Frequency v. Vd**



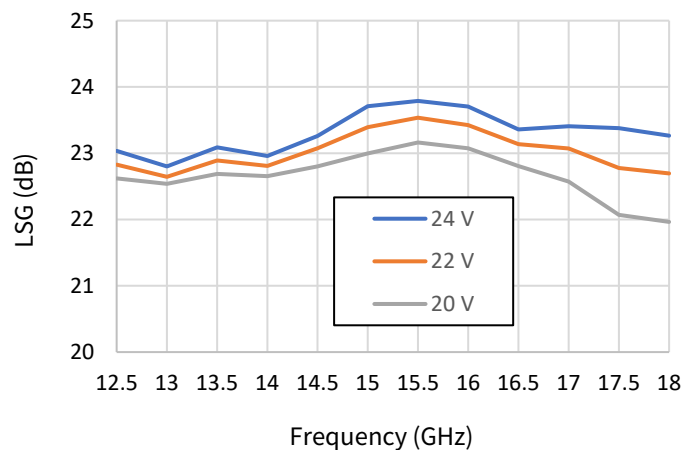
**Figure 10: Id v. Frequency v. Vd**



**Figure 11: Ig v. Frequency v. Vd**

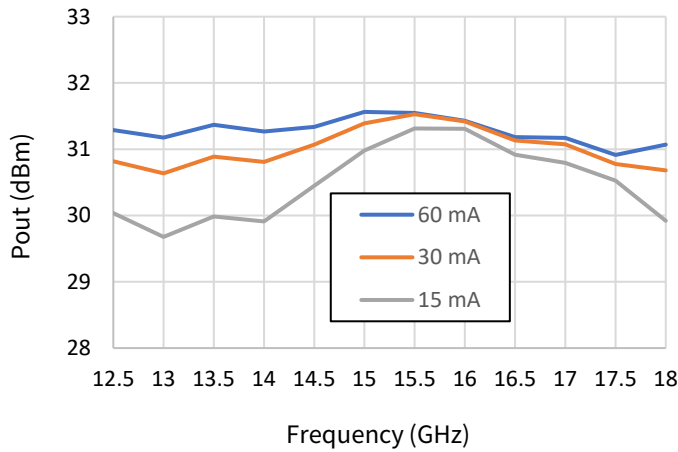


**Figure 12: LSG v. Frequency v. Vd**

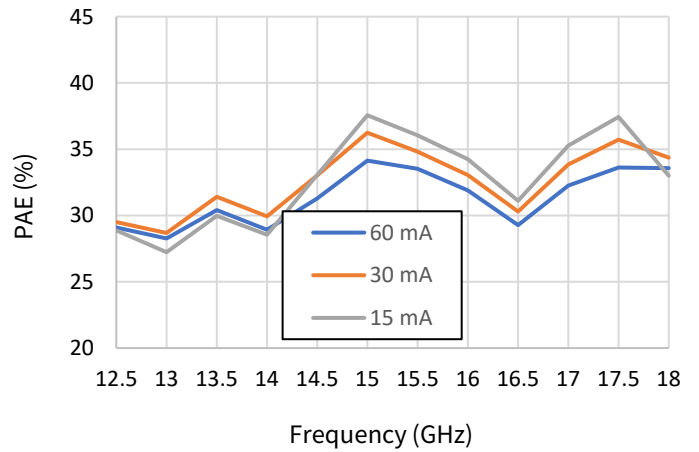


Test conditions unless otherwise noted: Vd=22 V, Idq=30mA, CW, Pin = 8 dBm, T<sub>base</sub>=25 °C, Frequency: 15.5GHz

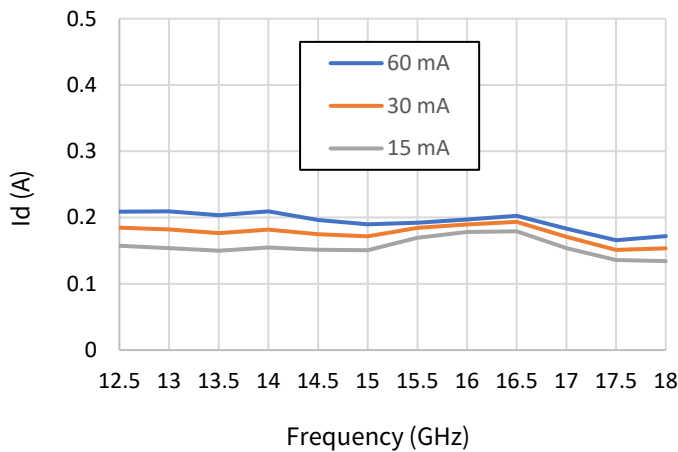
**Figure 13: Pout v. Frequency v. Idq**



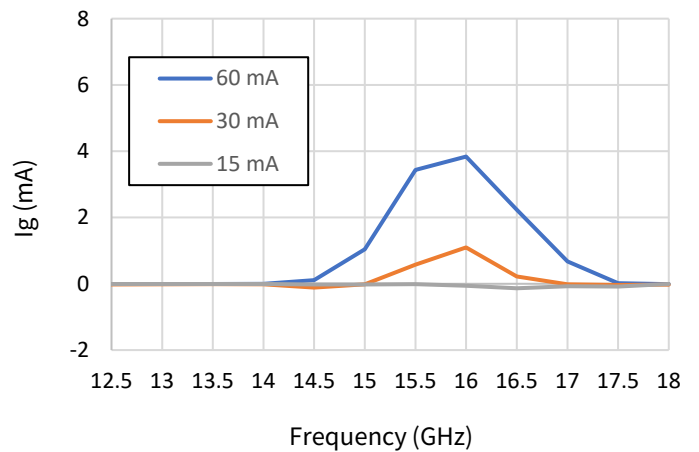
**Figure 14: PAE v. Frequency v. Idq**



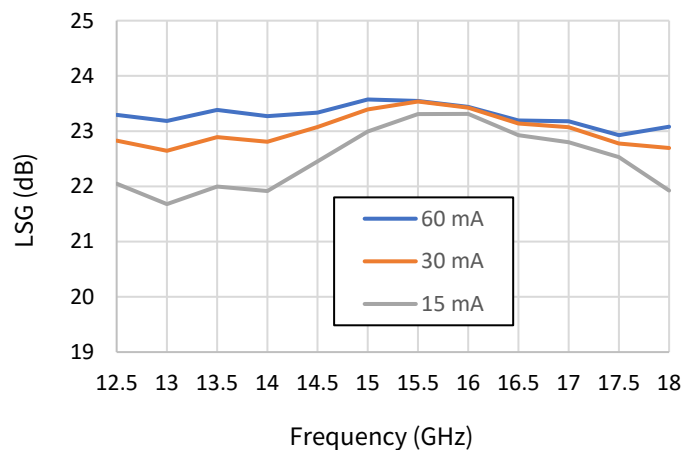
**Figure 15: Id v. Frequency v. Idq**



**Figure 16: Ig v. Frequency v. Idq**

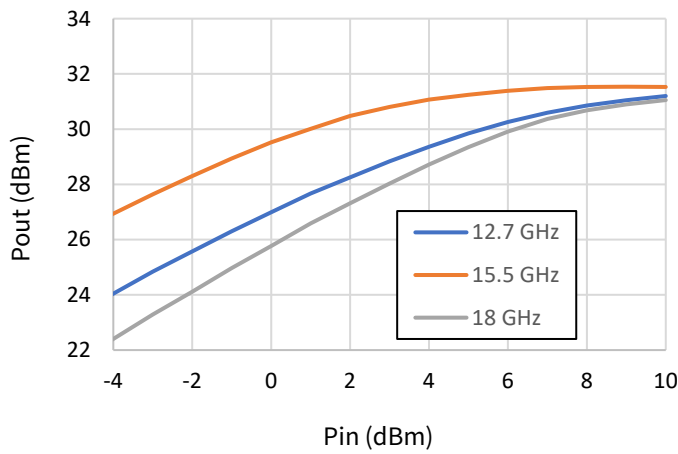


**Figure 17: LSG v. Frequency v. Idq**

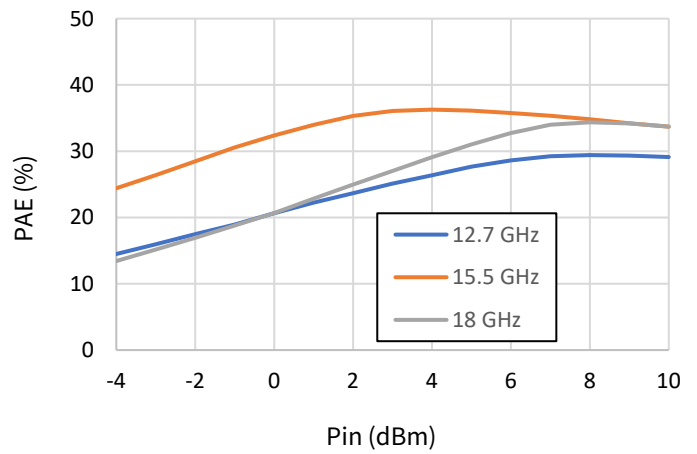


Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz

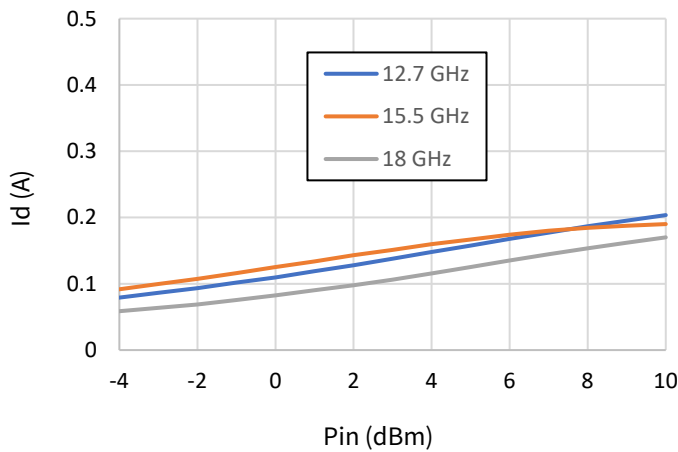
**Figure 18: Pout v. Pin v. Frequency**



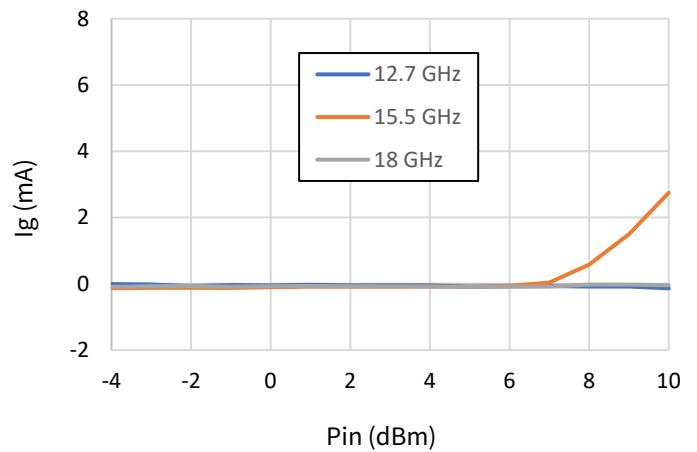
**Figure 19: PAE v. Pin v. Frequency**



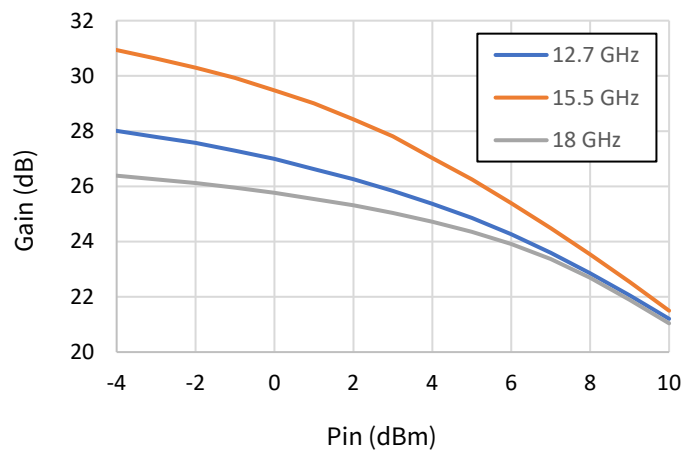
**Figure 20: Id v. Pin v. Frequency**



**Figure 21: Ig v. Pin v. Frequency**

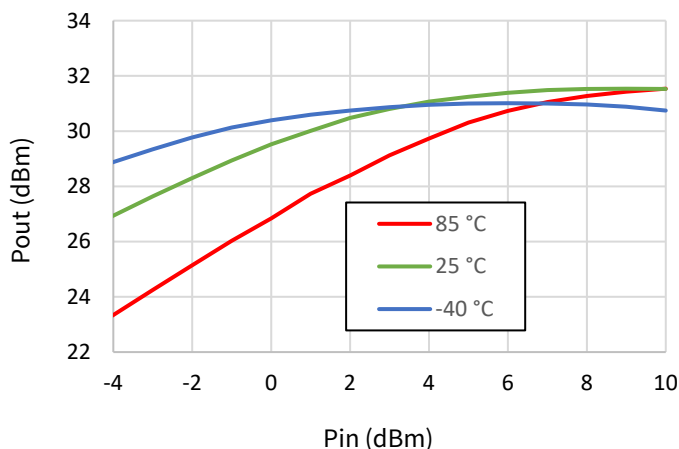


**Figure 22: Gain v. Pin v. Frequency**

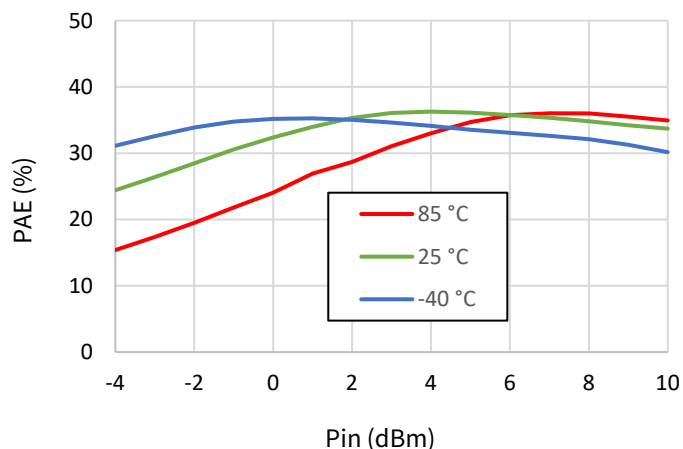


Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz

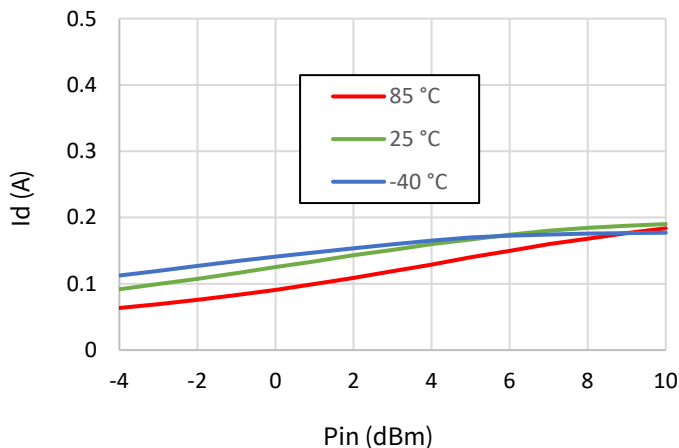
**Figure 23: Pout v. Pin v. Temperature**



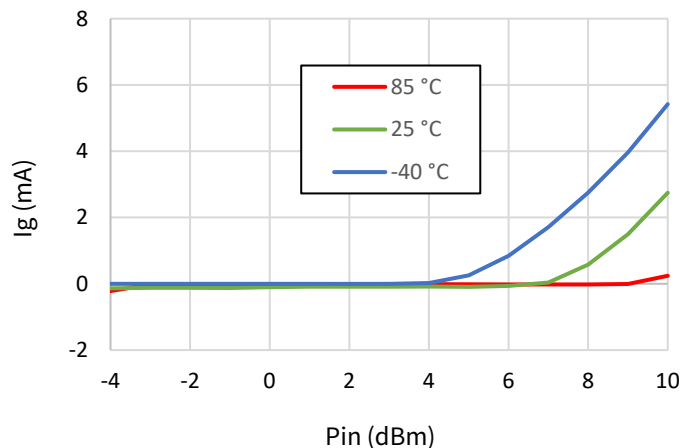
**Figure 24: PAE v. Pin v. Temperature**



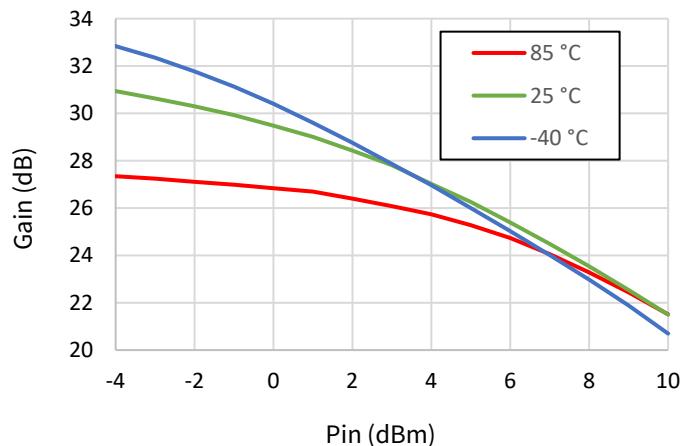
**Figure 25: Id v. Pin v. Temperature**



**Figure 26: Ig v. Pin v. Temperature**

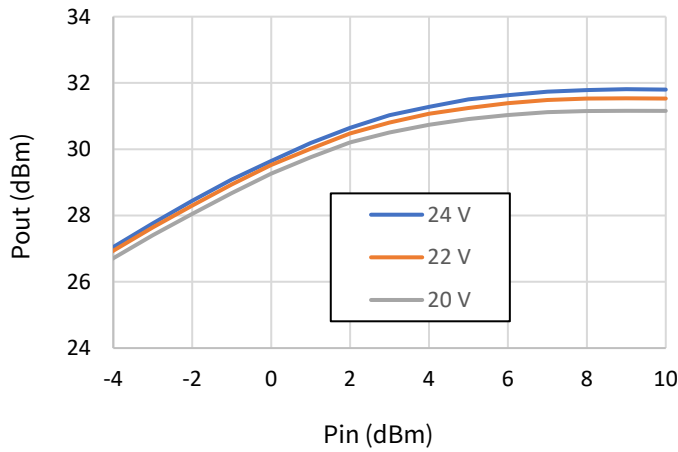


**Figure 27: Gain v. Pin v. Temperature**

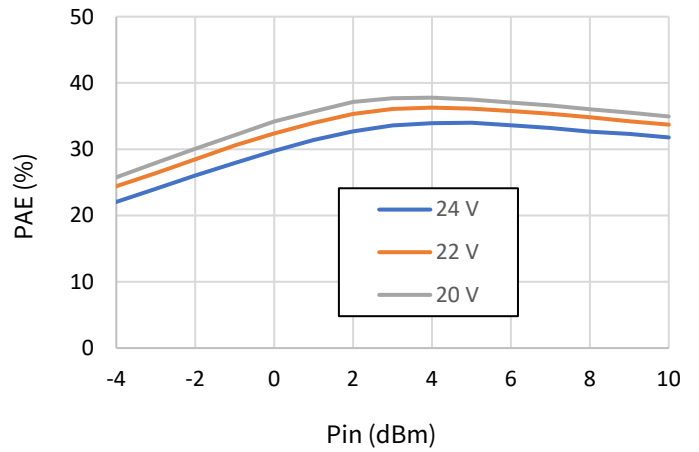


Test conditions unless otherwise noted: Vd=22 V, Idq=30mA, CW, Pin = 8 dBm, T<sub>base</sub>=25 °C, Frequency: 15.5GHz

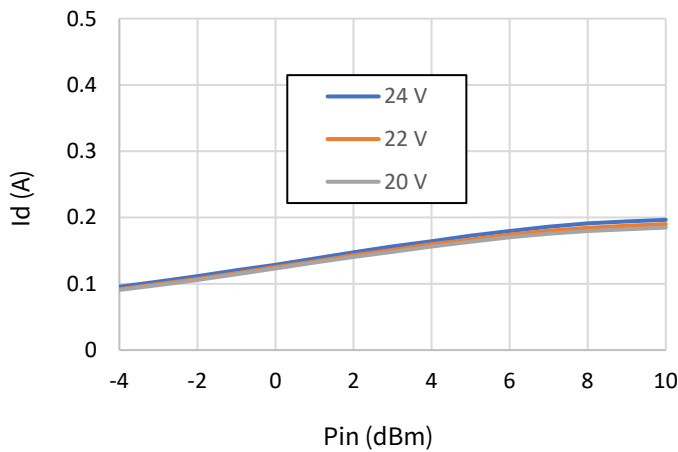
**Figure 28: Pout v. Pin v. Vd**



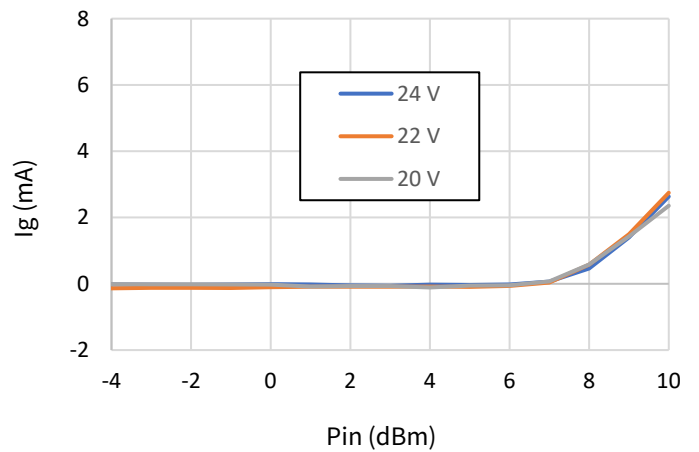
**Figure 29: PAE v. Pin v. Vd**



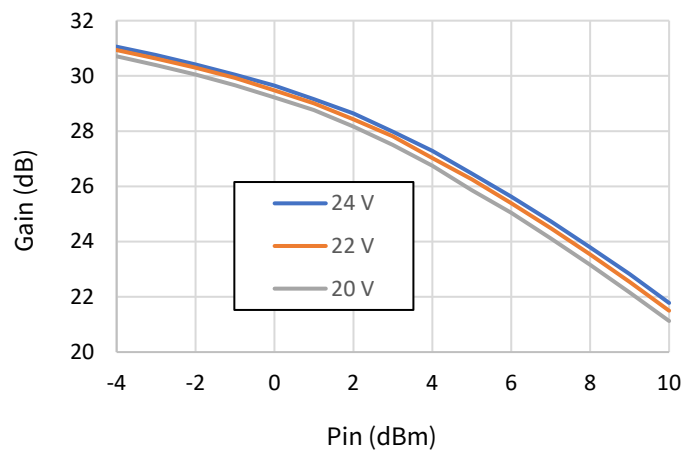
**Figure 30: Id v. Pin v. Vd**



**Figure 31: Ig v. Pin v. Vd**



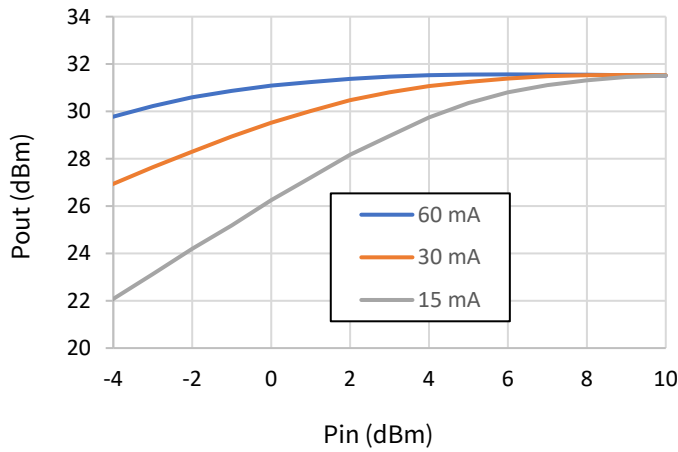
**Figure 32: Gain v. Pin v. Vd**



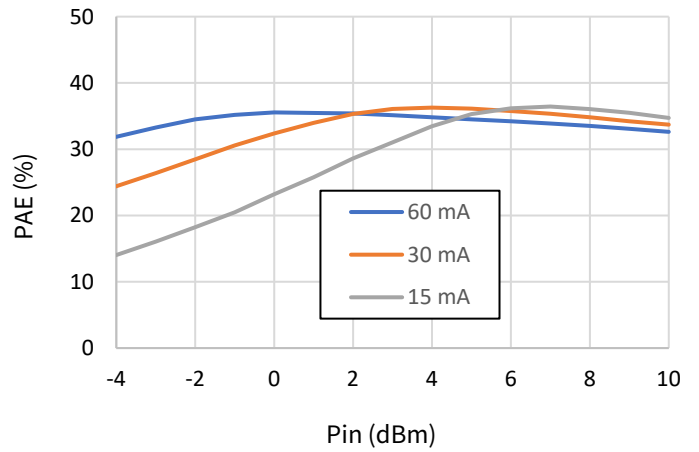


Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz

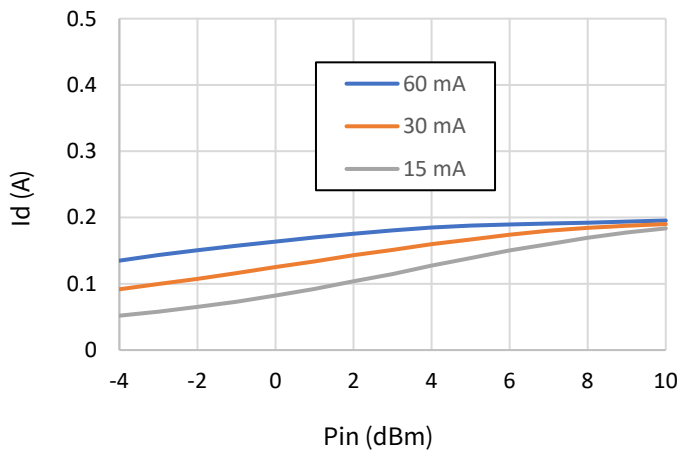
**Figure 33: Pout v. Pin v. Idq**



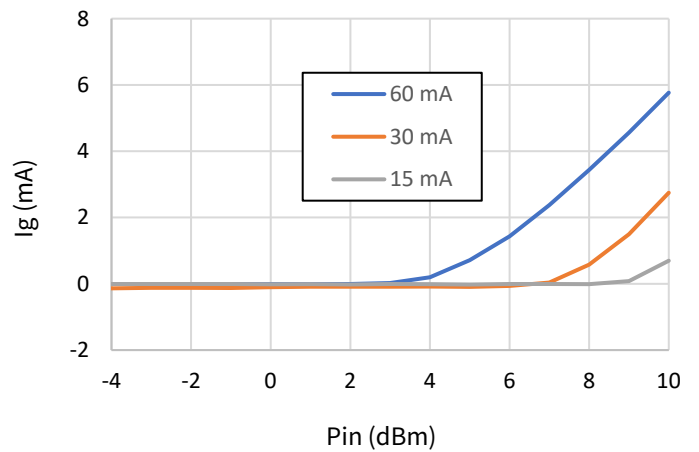
**Figure 34: PAE v. Pin v. Idq**



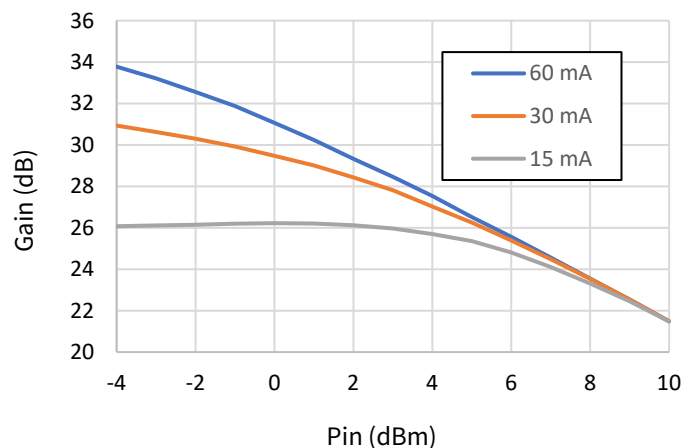
**Figure 35: Id v. Pin v. Idq**



**Figure 36: Ig v. Pin v. Idq**

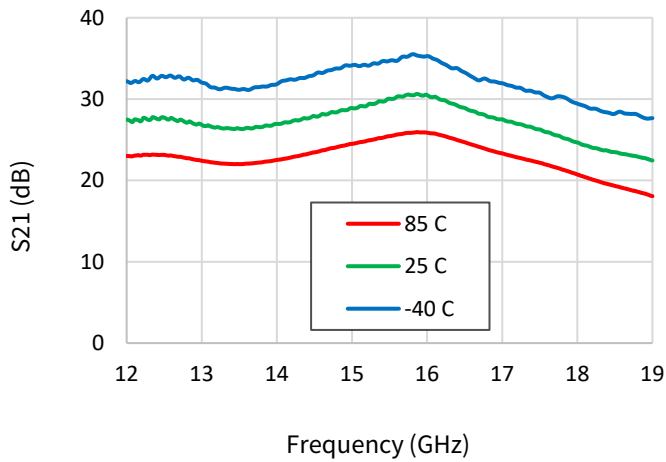


**Figure 37: Gain v. Pin v. Idq**

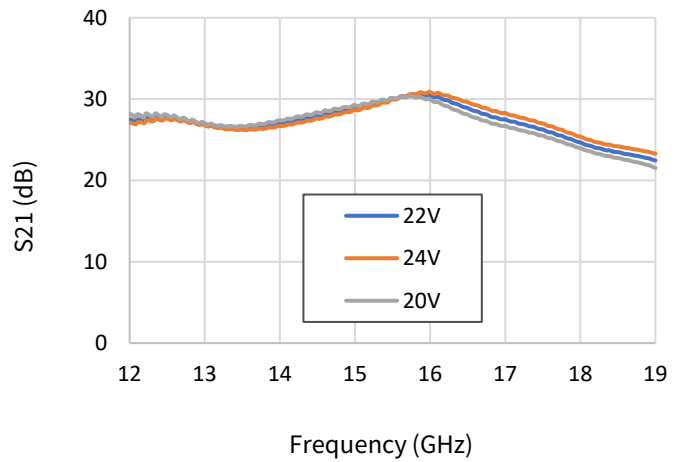


Test conditions unless otherwise noted: Vd=22 V, Idq=30mA, CW, Pin = 8 dBm, T<sub>base</sub>=25 °C, Frequency: 15.5GHz

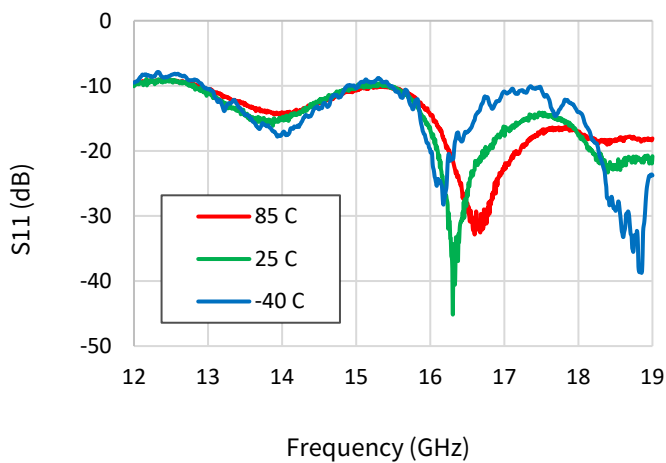
**Figure 38: S21 v. Frequency v. Temperature**



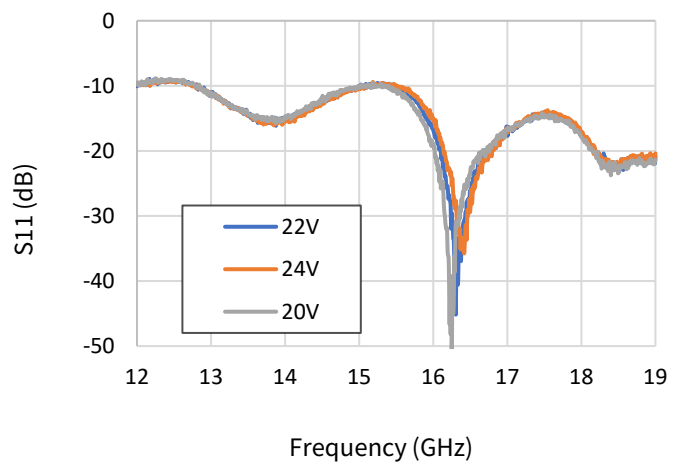
**Figure 39: S21 v. Frequency v. Vd**



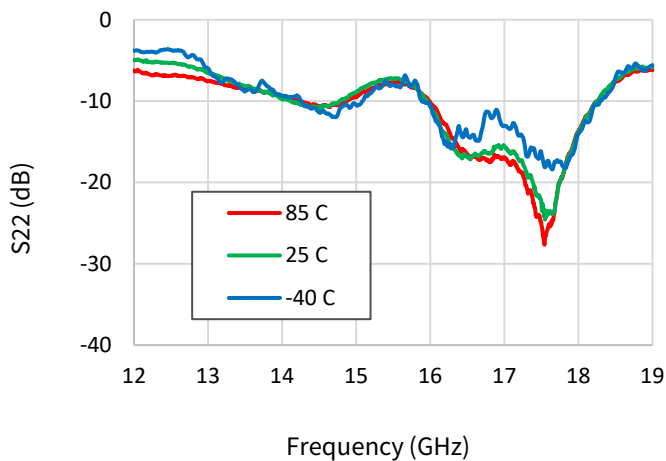
**Figure 40: S11 v. Frequency v. Temperature**



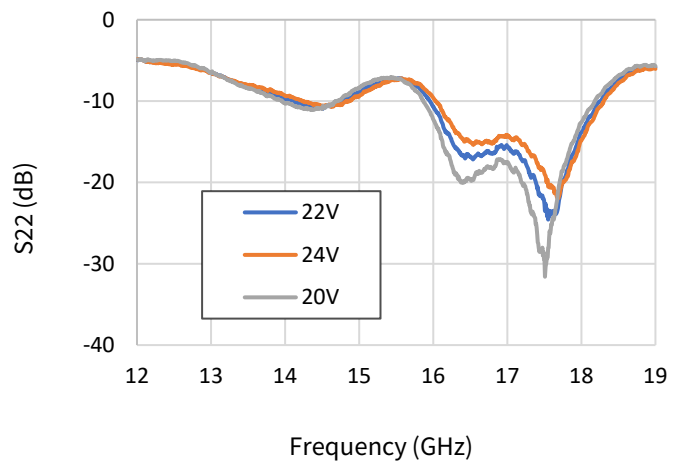
**Figure 41: S11 v. Frequency v. Vd**



**Figure 42: S22 v. Frequency v. Temperature**

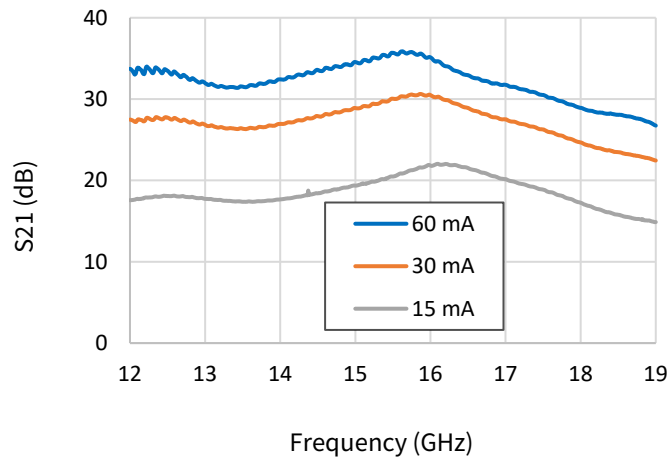


**Figure 43: S22 v. Frequency v. Vd**

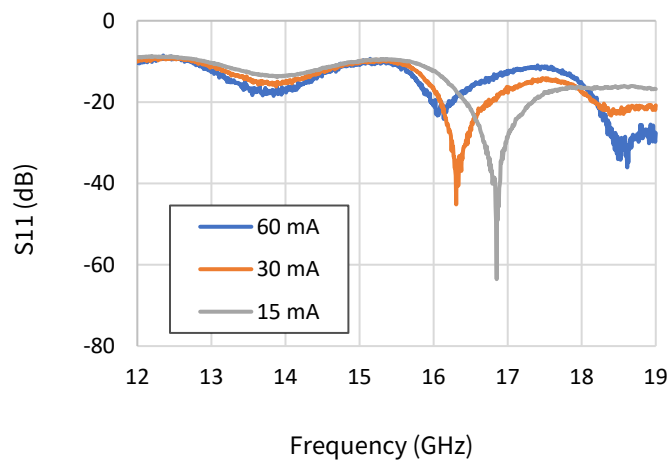


Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz

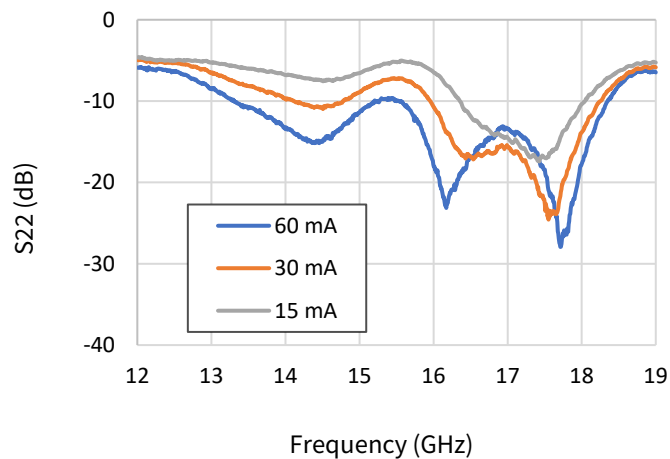
**Figure 44: S21 v. Frequency v. Idq**



**Figure 45: S11 v. Frequency v. Idq**

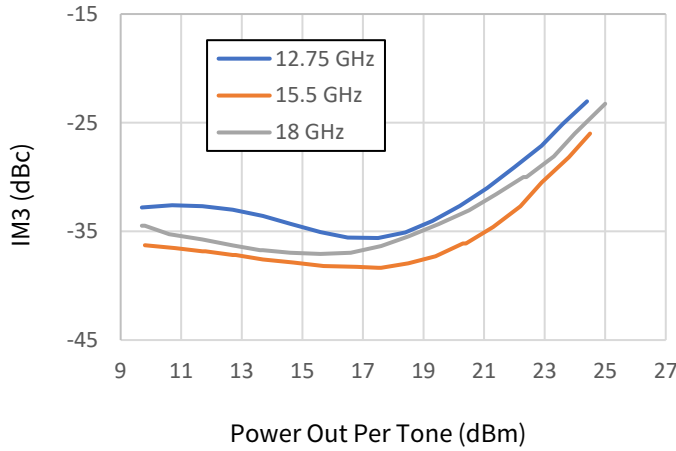


**Figure 46: S22 v. Frequency v. Idq**

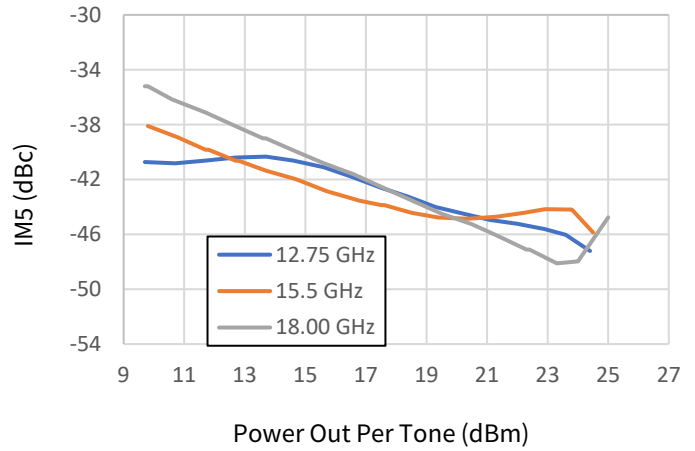


Test conditions unless otherwise noted:  $V_d=22\text{ V}$ ,  $I_{dq}=30\text{ mA}$ , CW,  $P_{in} = 8\text{ dBm}$ ,  $T_{base}=25\text{ }^\circ\text{C}$ , Frequency: 15.5GHz, Tone Spacing = 10 MHz,  $T_{base}=25\text{ }^\circ\text{C}$

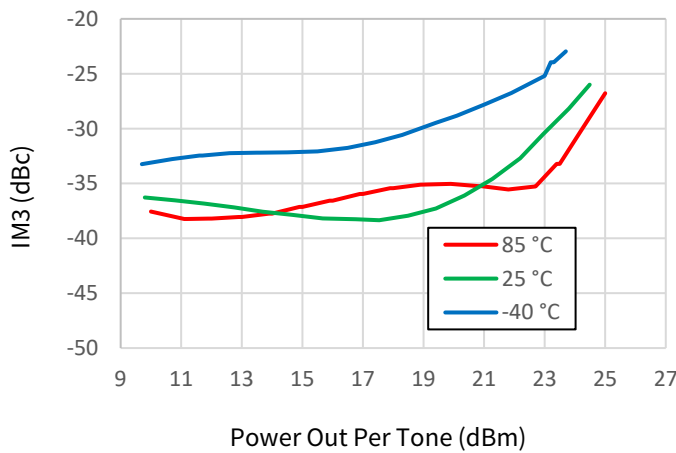
**Figure 47: IM3 v. Pout/tone v. Frequency**



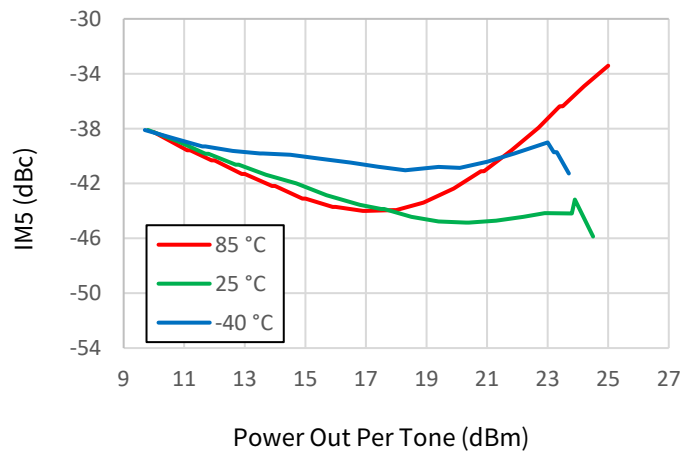
**Figure 48: IM5 v. Pout/tone v. Frequency**



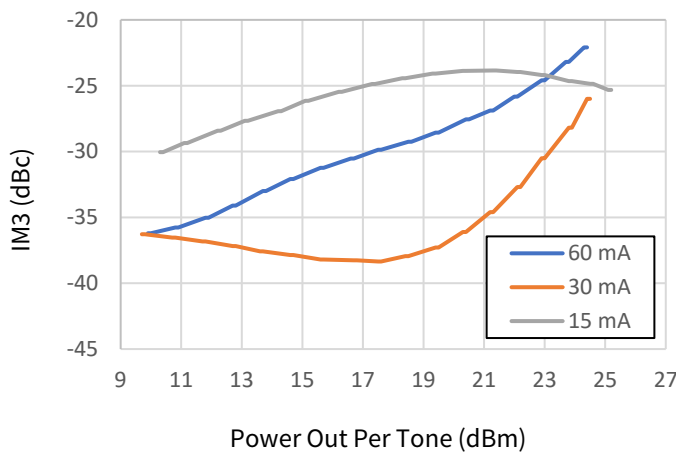
**Figure 49: IM3 v. Pout/tone v. Temperature**



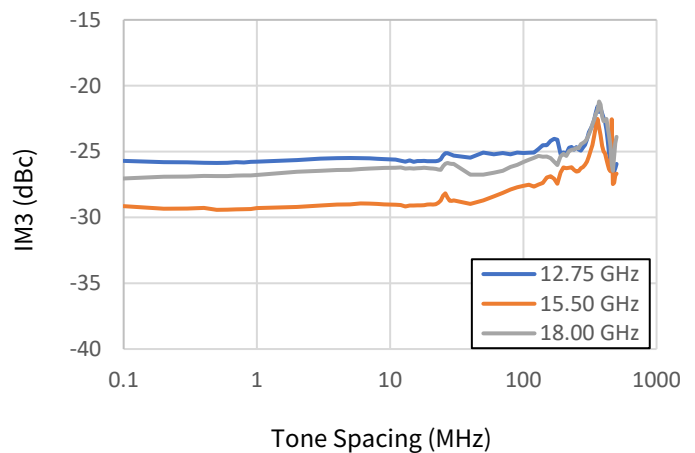
**Figure 50: IM5 v. Pout/tone v. Temperature**



**Figure 51: IM3 v. Pout/tone v. Idq**



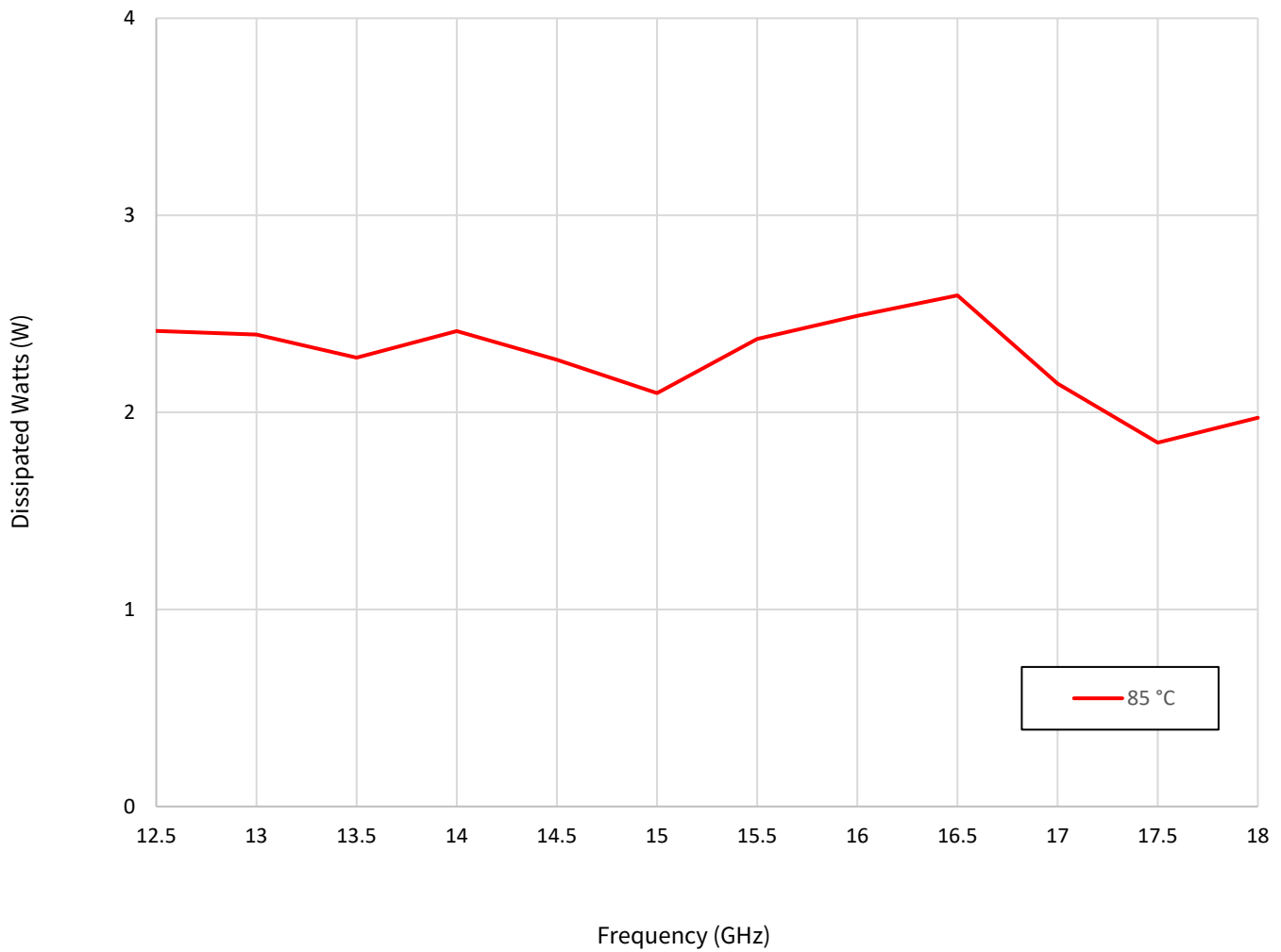
**Figure 52: IM3 v. Tone Spacing v. Frequency**



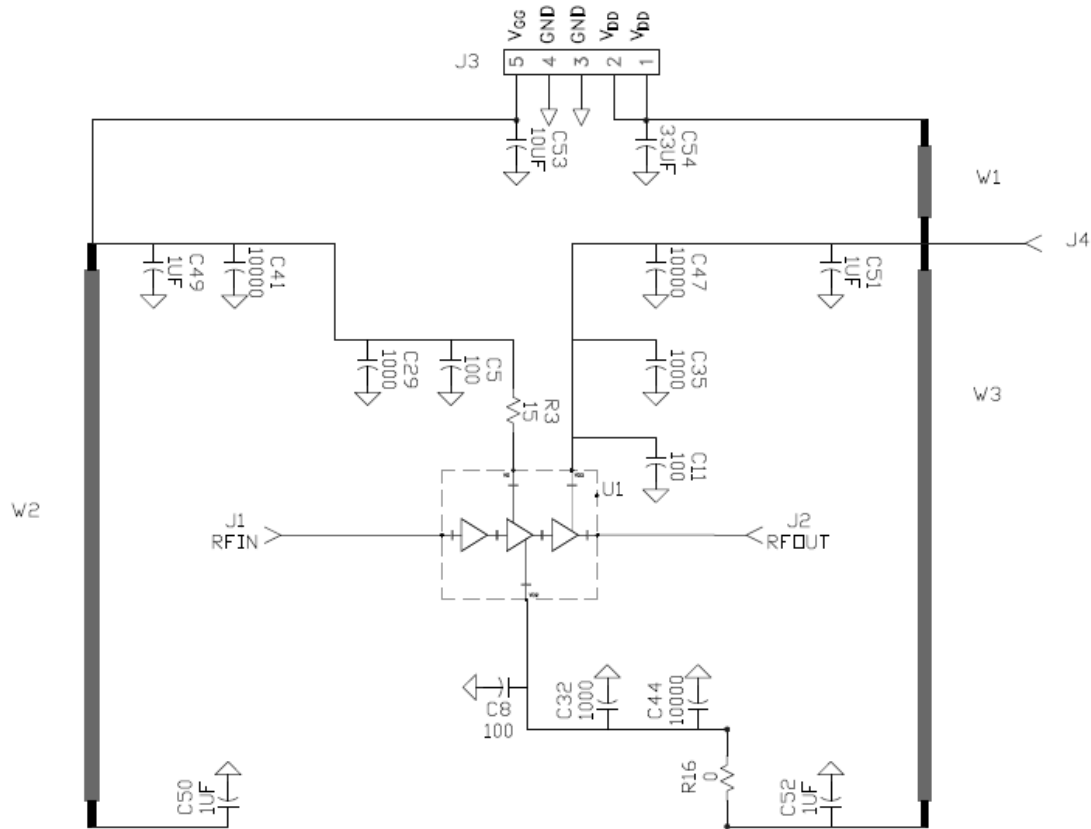
**Thermal Characteristics**

Parameter	Symbol	Value	Operating Conditions
Operating Junction Temperature	$T_J$	161.3	Freq = 15.5 GHz, $V_d = 22$ V, $I_{dq} = 30$ mA, $I_{drive} = 190$ mA, Pin = 8 dBm, $P_{out} = 31$ dBm, $P_{diss} = 2.4$ W, $T_{case} = 85^\circ\text{C}$ , CW
Thermal Resistance, Junction to Case	$R_{\theta JC}$	31.8	

**Power Dissipation v. Frequency ( $T_{case} = 85^\circ\text{C}$ )**



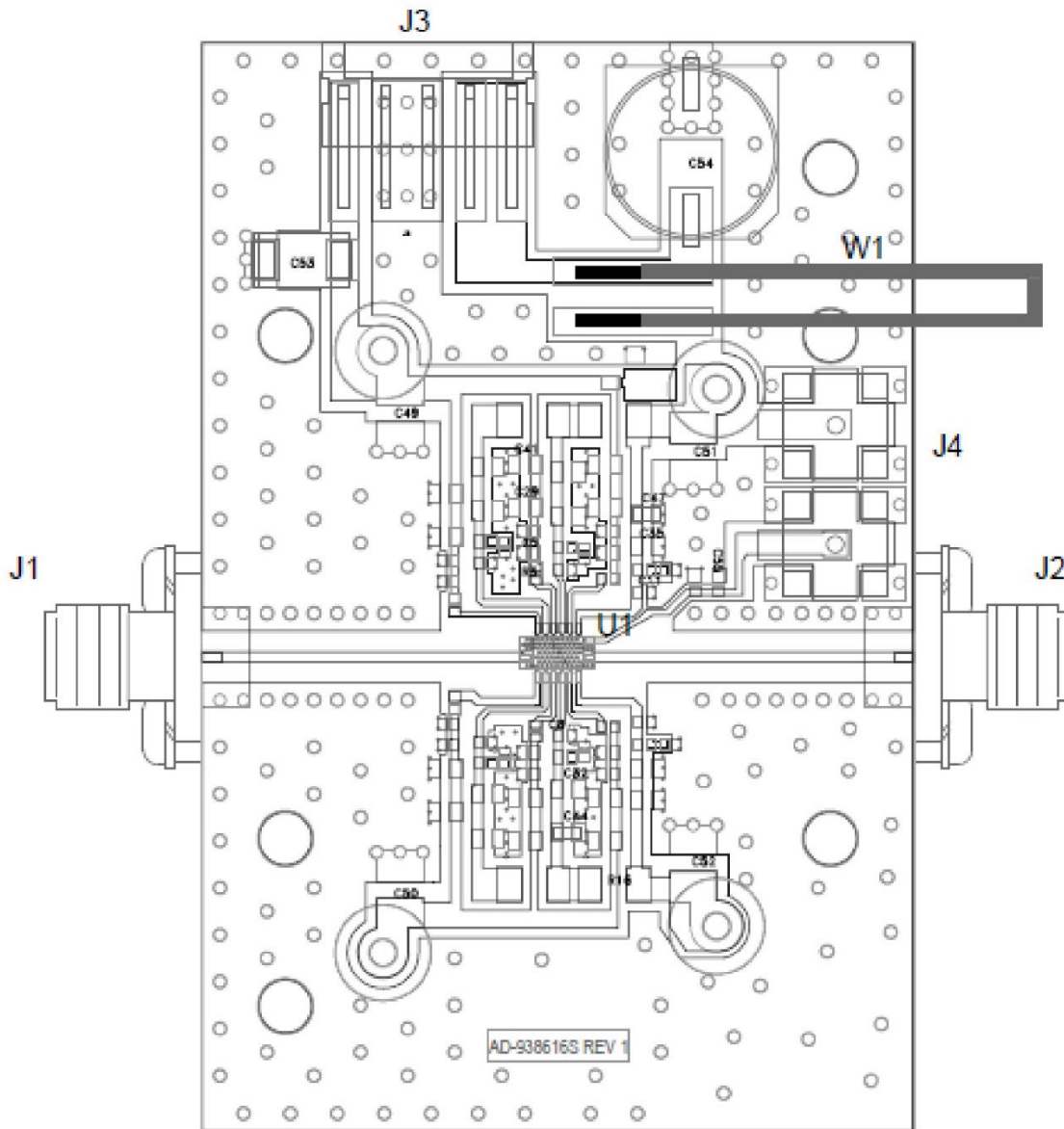
**CMPA1D1J001S-AMP1 Evaluation Board Schematic Drawing**



**CMPA1D1J001S-AMP1 Evaluation Board Bill of Materials**

Reference Designator	Description	Qty
C47, C41, C44	COG, 10nF, +/-5%, 100V, 0603	3
C54	CAP, 33 UF, 20%, G CASE	1
C53	CAP, 10UF, 16V, TANTALUM	1
C11, C55, C5, C8	CAP, 100pF, +/-5%, 50V, 0402	4
R3	RES 15 OHM, +/-1%, 1/16W, 0402	1
C35, C29, C32	CAP, 1000PF, +/-5%, 100V, 0603	3
C49, C50, C51, C52	CAP, 1UF, 100V	4
R16	RES 0.0 OHM 1/16W 1206 SMD	1
-	PCB, RF-35, .010 THK, 3X4, 3-STAGE, QFN, CMPA1D1J001S	1
-	BASEPLATE 2.6"x1.7"x0.25" AL 3x4 QFN	1
-	2-56 SOC HD SCREW 3/16 SS	4
-	#2 SPLIT LOCKWASHER SS	4
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST, 20MIL	2
J4	CONN, SMB, STRAIGHT JACK RECEPTACLE, SMT, 50 OHM, Au PLATED	1
J3	HEADER RT>PLZ .1CEN LK 5POS	1
W2, W3	WIRE, BLACK, 20 AWG	1
W1	WIRE, BLACK, 22 AWG	3
U1	CMPA1D1J001S	1

**CMPA1D1J001S-AMP1 Evaluation Board Assembly Drawing**



**Note:** W2 and W3 are connected on backside

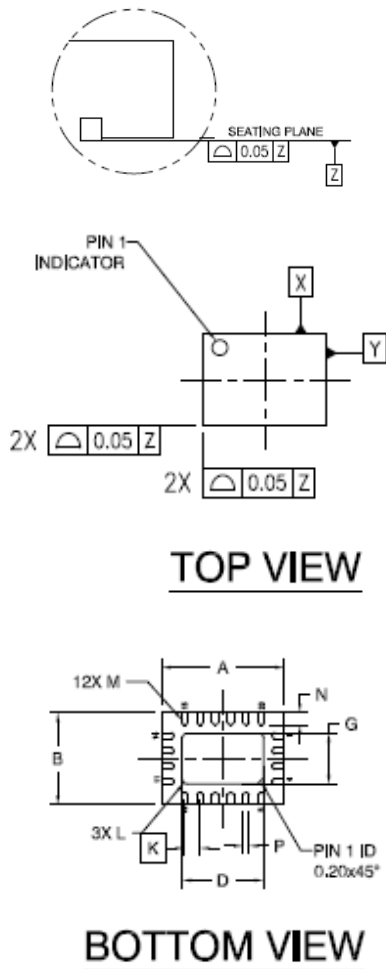
**Bias On Sequence**

1. Ensure RF is turned-off
2. Apply pinch-off voltage of -5 V to the gate ( $V_g$ )
3. Apply nominal drain voltage ( $V_d$ )
4. Adjust  $V_g$  to obtain desired quiescent drain current ( $I_{dq}$ )
5. Apply RF

**Bias Off Sequence**

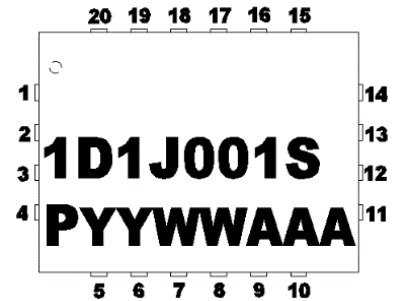
1. Turn RF off
2. Apply pinch-off to the gate ( $V_g = -5V$ )
3. Turn off drain voltage ( $V_d$ )
4. Turn off gate voltage ( $V_g$ )

**Product Dimensions**



NOTES: UNLESS OTHERWISE SPECIFIED

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
2. NUMBER OF LAND PADS: 20
3. THE CONTENTS OF THIS DRAWING ARE INTENDED TO REPRESENT THE PRODUCT IN MARKETING GRAPHICS ONLY AND NOT INTENDED TO BE USED FOR ANY PRODUCTION OR INTERNAL QUALIFICATION PURPOSE.



DIM	INCHES			MILLIMETERS		
	MIN	TYP	MAX	MIN	TYP	MAX
A	.156	.157	.159	3.95	4.00	4.05
B	.116	.118	.120	2.95	3.00	3.05
C	.033	.035	.037	0.85	0.90	0.95
D	.098	.104	.108	2.50	2.65	2.75
G	.059	.065	.069	1.50	1.65	1.75
K	—	.020	—	—	0.50	—
L	.004	.006	.008	0.10	0.15	0.20
M	.002	.003	.004	0.050	0.085	0.110
N	.012	.016	.020	0.30	0.40	0.50
P	.005	.008	.010	0.13	0.20	0.25
R	.000	.001	.002	0.00	0.02	0.05
S	—	.008	—	—	0.20	—

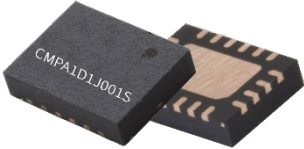
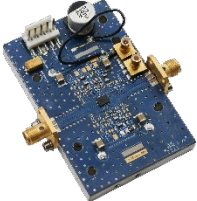
PIN	DESC	PIN	DESC
1	NC	11	RFGND
2	RFGND	12	RFOUT
3	RFIN	13	RFGND
4	RFGND	14	NC
5	NC	15	VD3
6	NC	16	NC
7	NC	17	NC
8	VD1,VD2	18	VG
9	NC	19	NC
10	NC	20	NC



## Electrostatic Discharge (ESD) Classification

Parameter	Symbol	Class	Classification Level	Test Methodology
Human body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

## Product Ordering Information

Part Number	Description	MOQ Increment	Image
CMPA1D1J001S	12.7 – 18 GHz, 1W GaN MMIC		
CMPA1D1J001S-AMP1	Evaluation Board w/ PA	1 Each	

## Notes & Disclaimer

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